



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	Ι _D Τ _A = +25°C
	0.15Ω @ V _{GS} = 4.5V	1.41A
12V	0.185Ω @ V _{GS} = 2.5V	1.25A
	0.21Ω @ V _{GS} = 1.8V	1.16A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- · Power management functions

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage V_{GS(TH)}, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)

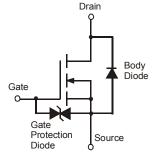
X1-DFN1006-3





Bottom View

Top View
Internal Schematic



Equivalent Circuit

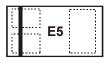
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMN1150UFB-7B	X1-DFN1006-3	10,000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



Top View

E5 = Product Type Marking Code Bar Denotes Gate and Source Side



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	12	V
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΙD	1.41 1.15	Α
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	7	Α
Maximum Body Diode continuous Current			Is	1	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

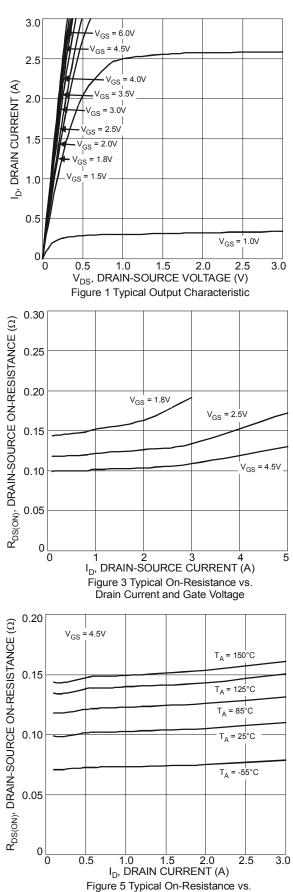
Characteristic	Symbol	Value	Units	
Total Dawar Dissination (Note 5)	T _A = +25°C	0	0.5	W
Total Power Dissipation (Note 5)	T _A = +70°C	P _D	0.3	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	251	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

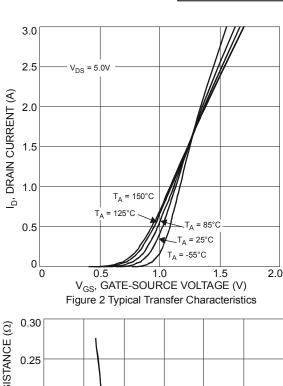
	T						
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	12	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	l	_	100	nA	$V_{DS} = 12V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±1	μΑ	$V_{GS} = \pm 6V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.35	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	150		$V_{GS} = 4.5V, I_D = 1A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	_	185	mΩ	$V_{GS} = 2.5V, I_D = 1A$	
			_	210		$V_{GS} = 1.8V, I_D = 1A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	106	_	pF	101/11/	
Output Capacitance	Coss	_	23	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	21	_	pF	1 - 1.0WHZ	
Gate resistance	R_{g}	_	92.4		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	l	1.5	l	nC		
Gate-Source Charge	Q_{gs}	_	0.2	_	nC	V _{DS} = 4V, I _D = 1A	
Gate-Drain Charge	Q_{gd}	_	0.2	_	nC		
Turn-On Delay Time	t _{D(on)}	_	4.1	-	ns		
Turn-On Rise Time	t _r	_	34.5		ns	$V_{DD} = 4V, V_{GS} = 6V, I_D = 1A$ $R_G = 1\Omega$	
Turn-Off Delay Time	t _{D(off)}	_	57	-	ns		
Turn-Off Fall Time	t _f	_	30	_	ns		

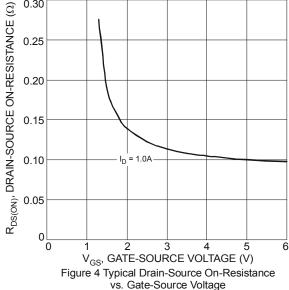
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.





Drain Current and Temperature





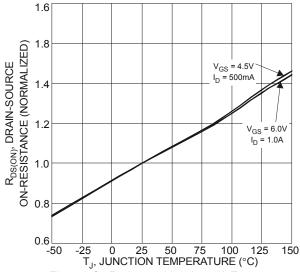
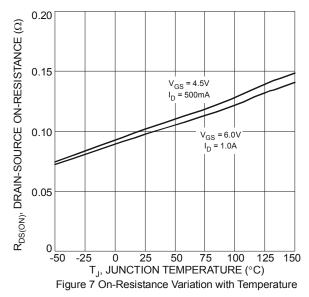
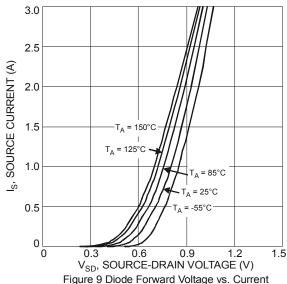
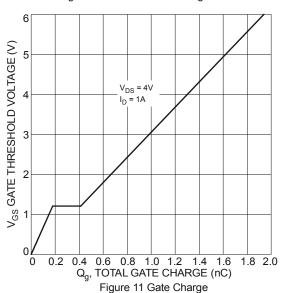


Figure 6 On-Resistance Variation with Temperature









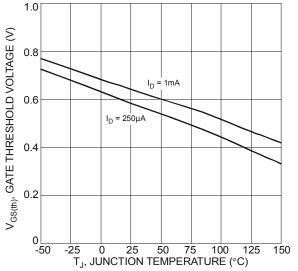
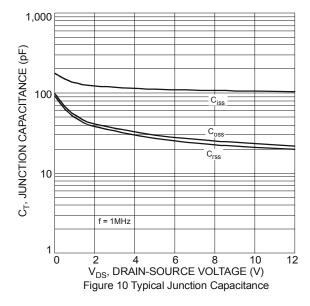
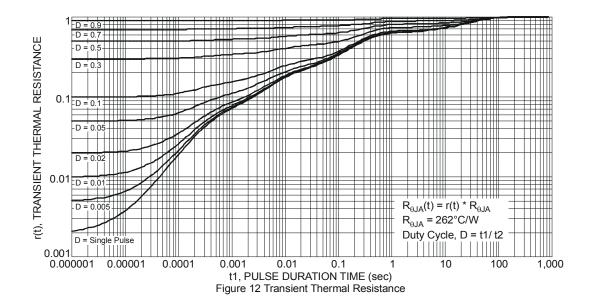


Figure 8 Gate Threshold Variation vs. Ambient Temperature

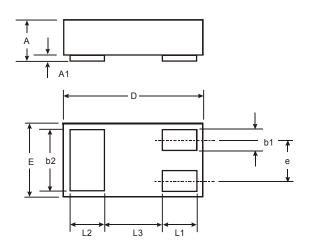






Package Outline Dimensions

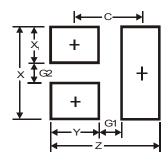
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е			0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	1.1		
G1	0.3		
G2	0.2		
Х	0.7		
X1	0.25		
Y	0.4		
С	0.7		



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